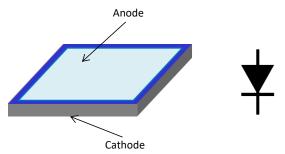
YJ Planar Schottky Barrier Diode Die Specification

30V 0.2A,13mil, Schottky barrier diode die based on silicon planar process

Part No.: PSB013T030AG-155A

Main Products Characterstics

- Average forward current: IF(AV) = 0.2 A
- Maximum operating junction temperature: Tj = 100 °C
- ESD rating: >2KV, per IEC61000-4-2 (Contact Discharge)
- Top metal: AL/3.915um



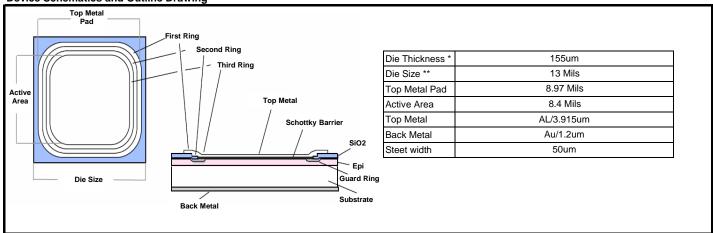
Maximum Ratings

Parameter	Symbol	Rating			
Repetitive peak reverse voltage	V_{RRM}	30 V			
Average forward current	$I_{F(AV)}$	0.2 A			
Non-repetitive peak surge current (tp = 8.3 ms, halfwave, 1 cycle)	I _{FSM}	1 A			
Storage temperature range	T _{stg}	-50 to +100 °C			
Maximum operating junction temperature	T _j	100 °C			

Static Electrical Characteristics (Ta = 25°C)

Parameter	Symbol	Value		
Farameter		Spec	Typical	
Reverse breakdown voltage $I_R = 100 \text{uA}$	V_{BR}	33V	48V	
Maximum forward voltage drop				
I _F =200mA	V_{F}	0.5V	0.43V	
Pulse Test: tp = 800 μ s, $\delta \leqslant 2\%$				
Maximum reverse current V_R = 10V Pulse Test: tp = 200 μ s, $\delta \leqslant 2\%$	I _R	30u'A	11uA	

Device Schematics and Outline Drawing



Important Notice

Specification apply to die only. Actual performance may degrade when assembled.

Yangie Electronics does not guarantee device performance after assembly.

All operating parameters must be validated for each customer application by customer's technical experts.

Data sheet information is subjected to change without notice.

Recommended Storage Environment:

Store in original container, in dessicated nitrogen, with no contamination.

Shelf life for parts stored in above condition is 2 years.

If the storage is done in normal atmosphere shelf life is reduced to 6 months.

Yangzhou Yangjie Electronics Technology Co.,Ltd.

电话: 0514-80982389

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